

Supplementary Information

A Novel Route to High-Quality Graphene Quantum Dots by Hydrogen-Assisted Pyrolysis of Silicon Carbide

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KEYWORDS: graphene quantum dots; silicon carbide; hydrogen-assisted pyrolysis; high-quality

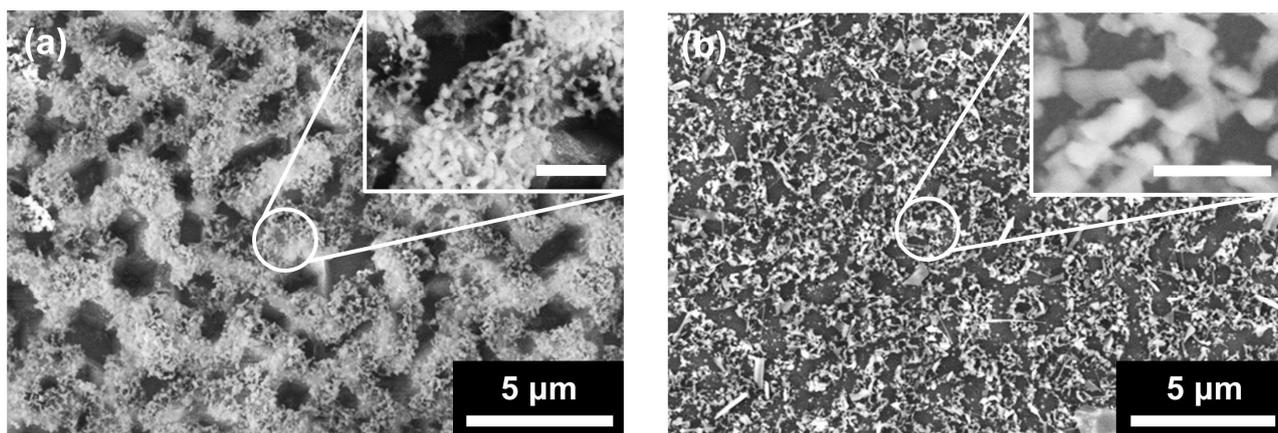


Figure S1. FE-SEM image of GQDs on SiC plate after annealed at 1500 °C with various operating hydrogen etching gas pressure. The operating pressure was (a) 120 mTorr (inset scale bar is 1 μm) and (b) 160 mTorr (inset scale bar is 1 μm).

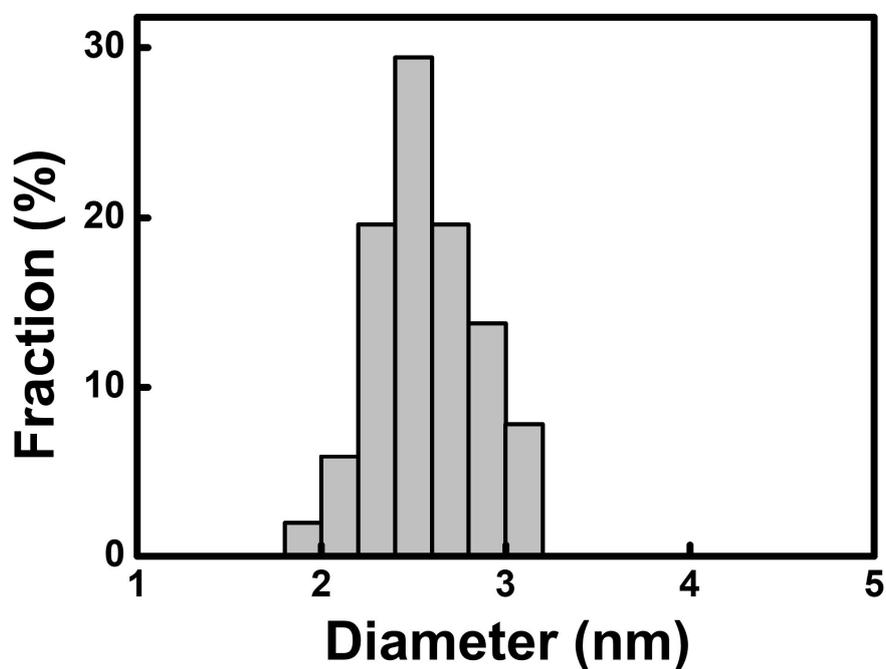


Figure S2. Size distribution of fabricated GQDs.

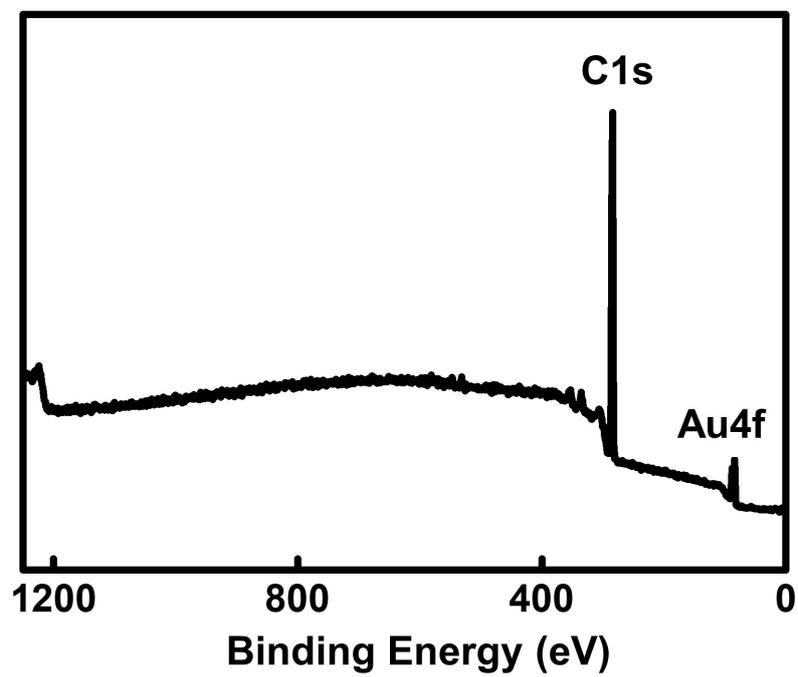


Figure S3. X-ray photoelectron spectroscopy (XPS) survey spectrum of the fabricated high-quality GQDs.